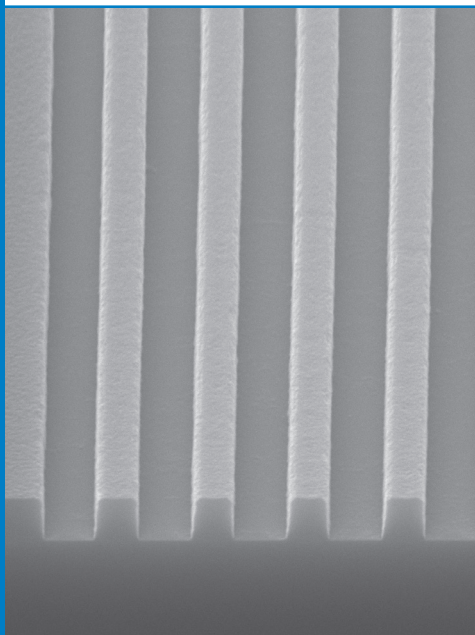


Positive Photoresists for UV, Laser & Greyscale Lithography



- **ma-P 1200 series, ma-P 1275HV**
for standard UV lithography
- **ma-P 1200G series** for greyscale lithography
- **ma-P 1200LIL series**
for laser interference lithography

Unique features of the positive photoresists

- Designed for - UV Lithography (mask aligner, laser grey-scale lithography, laser interference lithography)
- No post exposure bake
- Easy removal
- Ready-to-use resist solutions in a variety of viscosities

- Made in Germany -



SCAN ME

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March 2024

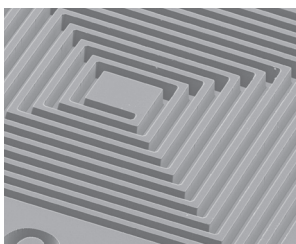
Positive Photoresist Series and Thick Film Photoresists for UV lithography

Resist		ma-P 1200 series	ma-P 1275	ma-P 1275HV
Spectral sensitivity	nm	330 - 450	350 - 450	350 - 450
Ready-to-use solutions for various film thicknesses	μm	ma-P 1205 → 0.5 ma-P 1210 → 1.0 ma-P 1215 → 1.5 ma-P 1225 → 2.5 ma-P 1240 → 4.0 ma-P 1275 → 7.5 @ 3000 rpm	6 - 40 in one spin-coating step	10 - 60 in one spin-coating step
Exposure dose @ 365 nm*	mJ cm ⁻²	35 - 150	150 - 3000	300 - 4000
Developer		ma-D 331 & ma-D 331/S (NaOH based); mr-D 526/S (TMAH based)		

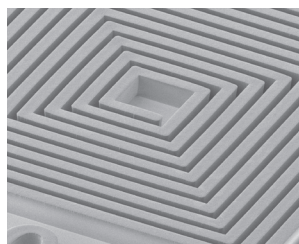
* Mask aligner broadband exposure

Resist patterning with mask aligner broadband exposure and pattern transfer

Resist mould for electroplating

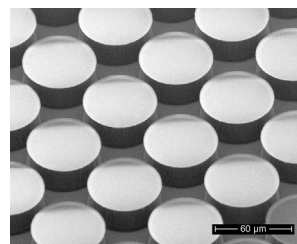


56 μm ma-P 1275HV mould

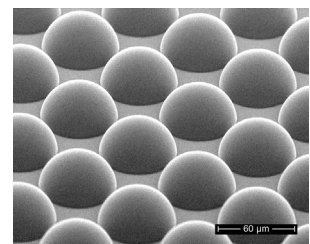


48 μm electroplated Ni

Resist pattern reflow



20 μm ma-P 1275,
60 μm diameter pillar

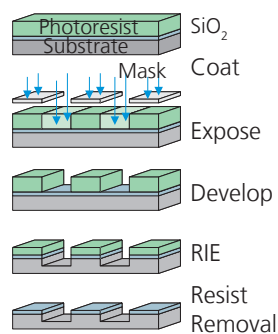


30 μm reflowed ma-P 1275,
60 μm diameter

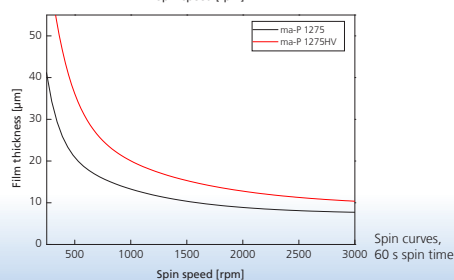
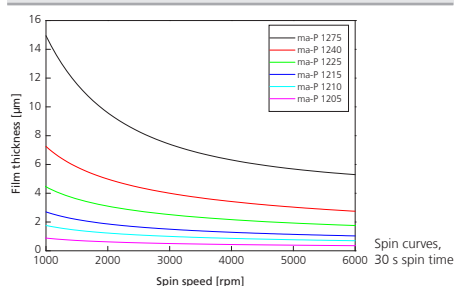
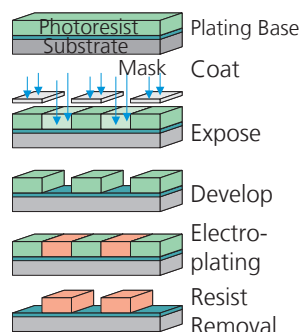
ma-P 1200 series and ma-P 1275 & ma-P 1275HV for microsystems technology and microelectronics

- Film thickness up to 50 μm
- Broadband-, g- and i-line exposure
- High stability in acid and alkaline plating baths
- High dry and wet etch resistance
- Good thermal stability of the resist patterns attainable
- Aqueous alkaline development
- Side wall angle up to 87° with mask aligner broadband exposure
- Suitable for pattern reflow

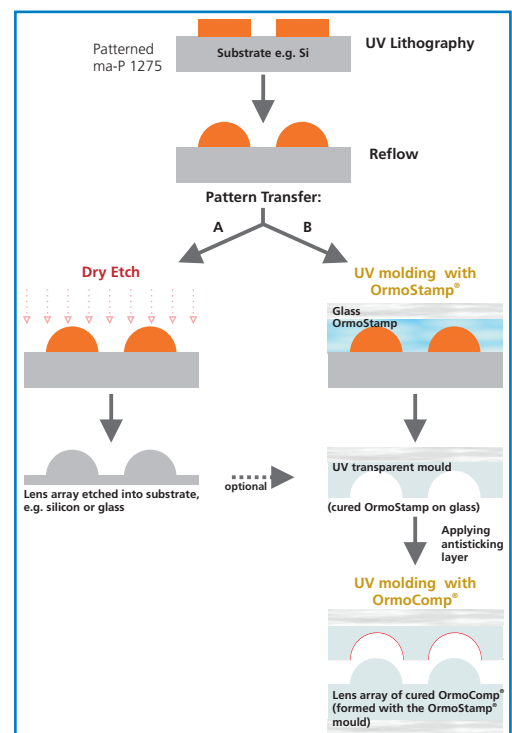
Process flow RIE



Process flow Electroplating



Reflow of ma-P 1200/ ma-P 1200G and pattern transfer



Main applications

- Etch mask - metals and semiconductors
- Mould for electroplating
- Fabrication of micro optical components, e.g. micro lenses by pattern transfer from reflowed resist patterns
- Mask for ion implantation

Positive Photoresist Series for Greyscale Lithography

Resist		ma-P 1215G	ma-P 1225G	ma-P 1240G	ma-P 1275G			
Film thickness *	µm	1.5	2.5	4.0	9.5	15	30	60
Spin-coating	rpm s	3000 30	3000 30	3000 30	3000 30	1500 30	500 60	1000 4
Spectral sensitivity	nm	350 - 450						
Exposure dose @ 365 nm**	mJ cm ⁻²	50 - 70	70 - 110	120 - 160	150 - 5000			
Developer		ma-D 532/S, mr-D 526/S (TMAH based) for greyscale lithography ma-D 331 (NaOH based) for standard lithography						

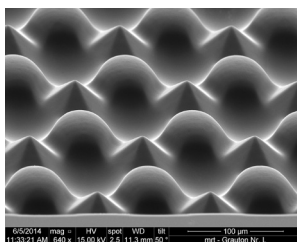
* Resists with different viscosities available as custom-made products

** Mask aligner broadband exposure

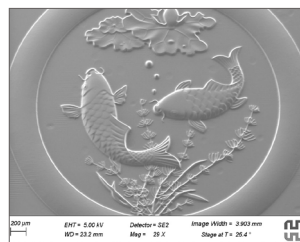
Resist patterning with Laser Direct Writing

* Patterned at Heidelberg Instruments

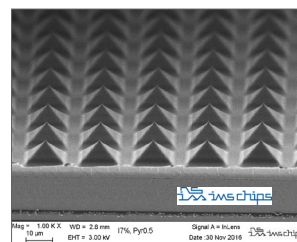
** by courtesy of IMS CHIPS



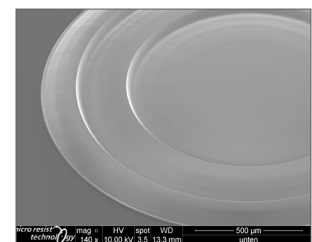
Convex and concave hexagonal lenses, 60 µm diameter*



Test pattern, 63 µm pattern depth*



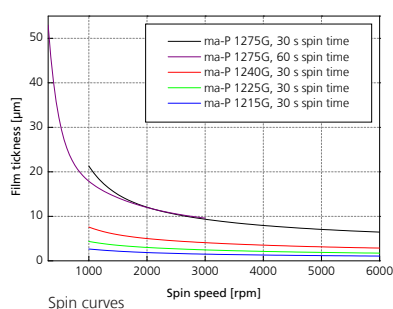
Pyramids, 10 µm base width, 5 µm height, 45 °angle**



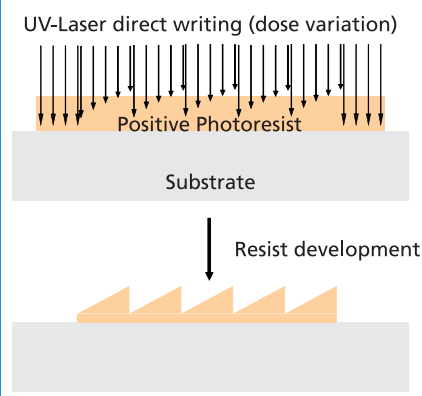
Fresnel lens, 2 mm diameter, patterned in ma-P 1275G

ma-P 1200G for greyscale lithography

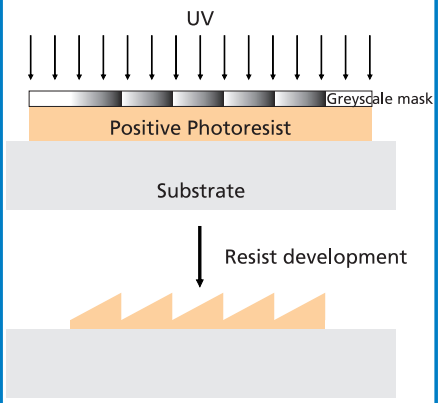
Specifically designed for the requirements of **greyscale lithography**, application in standard binary lithography also possible.



Process flow Laser Direct Writing



Process flow Exposure through a greyscale mask



- Reduced contrast, also in thin films
- Film thickness 1 - 60 µm and higher
- Reduced outgassing at laser exposure with higher intensity
- Max. 70 - 80 µm greyscale pattern depth possible
- Aqueous alkaline development
- Suitable for pattern reflow after standard binary lithography

Main applications

Use of manufactured 3D patterns in microoptics, MEMS and MOEMS and displays

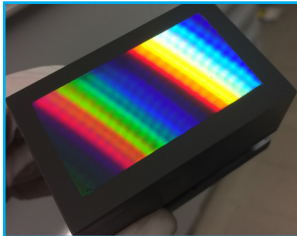
Pattern transfer by

- UV and thermal moulding
- Electroplating
- Etching

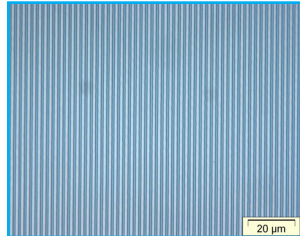
Thin Film Positive Photoresists in Laser Interference Lithography

Resist		mr-P 1201LIL	mr-P 1202LIL
Film thickness @ 3000 rpm	μm	0.1	0.2
Spin coating	rpm	3000	
Spectral sensitivity	nm	330 – 450	
Exposure dose @ 405 nm	mJ cm^{-2}	15 – 50	
Developer		mr-D 374/S (metal ion bearing, silicate/ phosphate based)	

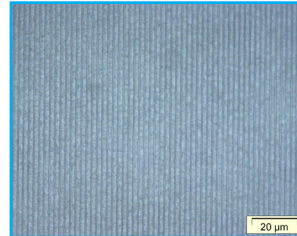
Resist patterning with laser interference lithography



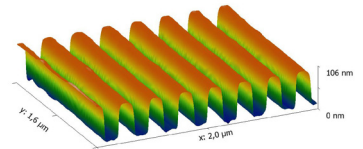
Diffraction optic: laminar grating (50 x 30 mm²), 170 nm thick mr-P 1202LIL, 400 lines/ mm



mr-P 1202LIL, 400 lines/ mm



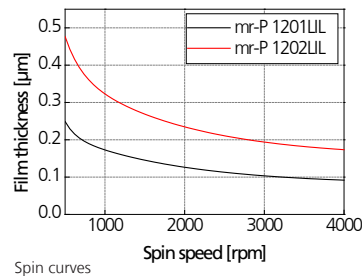
Si pattern after RIE etching, 400 lines/ mm



100 nm thick mr P 1201LIL, 125 nm pattern width

mr-P 1200LIL for high resolution laser interference lithography

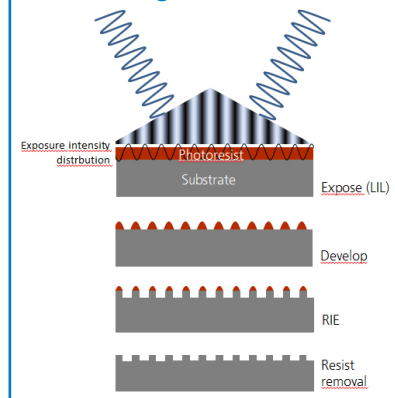
- Steep sidewalls due to high contrast enable high quality etched pattern
- Good etch resistance
- Film thickness 100....500 nm



Main applications

- Masking of substrate surface during fabrication of steep-edged nano structures for diffractive optics:
- Laminary gratings
- VLS gratings

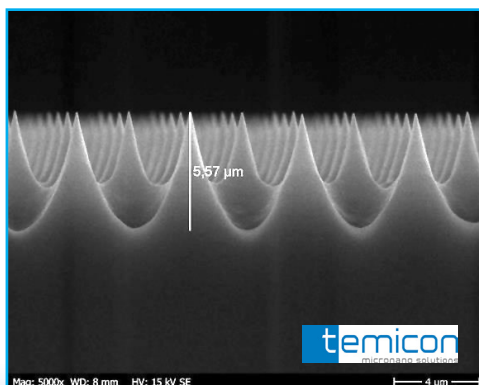
Process flow Laser Interference Lithography and etching



Greyscale photoresists in special applications

mr-P 1200G in laser interference lithography

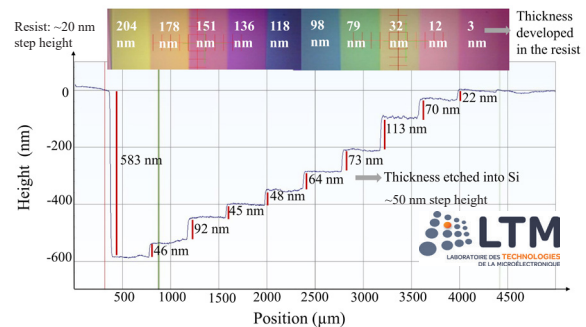
Moth eye patterns for pattern transfer; 10 μm thick ma-P 1275G patterned by Laser Interference Lithography @ 351 nm; 5.6 μm pattern depth



by courtesy of temicon GmbH

mr-P 1200G for very high vertical pattern resolution

Si staircase structure for Fabry-Perot μ -interferometers array; 500 nm thick ma-P 1200G resist patterned by Laser Direct Writing @ 405 nm¹⁾



by courtesy of LTM, CNRS/ Univ. Grenoble Alpes

¹⁾ N. Gerges, C. Petit-Etienne, M. Panabière, J. Boussey, Y. Ferrec, C. Gourgon; Optimized ultraviolet greyscale process for high vertical resolution applied to spectral imagers; J. Vac. Sci. Technol. B 39 (2021); doi: 10.1116/6.0001273